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1. Name of conveying party(ies)
Citicorp USA, Inc.

Additional name(s) of conveying party(ies) attached? Yes No

2. Name and address of receiving party(ies)
Name: MEMC Electronic Materials, Inc.
Internal Address: _____

3. Nature of conveyance/Execution Date(s):
Execution Date(s) 08/02/2005

Assignment Merger
 Security Agreement Change of Name
 Joint Research Agreement
 Government Interest Assignment
 Executive Order 9424, Confirmatory License
 Other Release of Security Interests

Street Address: 501 Pearl Drive
 City: St. Peters
 State: MO
 Country: USA Zip: 63376

Additional name(s) & address(es) attached? Yes No

4. Application or patent number(s): This document is being filed together with a new application.

A. Patent Application No.(s)
09/370,349; 09/704,893; 09/489,481; 09/659,537; 09/704,900;
09/730,171, 09/730,172; 09/535,759; 09/737,715 (cont'd)

B. Patent No.(s)
4,395,389; 4,450,960; 4,532,120; 4,554,141; 4,608,096; 4,622,082;
4,632,816; 4,666,532; 4,668,330 (cont'd)

Additional numbers attached? Yes No

5. Name and address to whom correspondence concerning document should be mailed:

Name: Roxana Wizorek
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 Street Address: 211 North Broadway, Suite 3600
 City: St. Louis
 State: MO Zip: 63102-2750
 Phone Number: 314/259-2699
 Fax Number: 314/259-2020
 Email Address: rwizorek@bryancave.com

6. Total number of applications and patents involved: 268

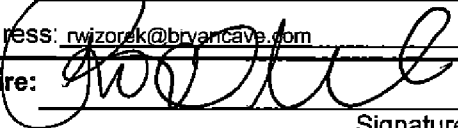
7. Total fee (37 CFR 1.21(h) & 3.41) \$ 10,720.00

Authorized to be charged by credit card
 Authorized to be charged to deposit account
 Enclosed
 None required (government interest not affecting title)

8. Payment Information

a. Credit Card Last 4 Numbers _____
Expiration Date _____

b. Deposit Account Number 02-4467
Authorized User Name Roxana Wizorek

9. Signature: 
Signature
Roxana Wizorek
Name of Person Signing

Date: 8/11/2005

Total number of pages including cover sheet, attachments, and documents: 37

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CH \$10720.00 024467 09370349

CONTINUATION OF ITEM 4:

4A. Patent Application Numbers CONT'D.

08/971,253
08/991,799
09/833,777
09/816,015
09/475,320
09/270,366
09/705,092
09/874,487
09/859,094
09/082,906
09/667,909
09/332,745
09/691,994
09/344,003
09/344,036
09/853,232
09/344,709
09/352,980
09/366,850
09/372,897
09/379,383
09/929,585
09/385,108
09/416,998
09/419,151
09/430,654
09/438,551
09/481,080
09/506,105
09/495,563
09/502,340
09/503,566
09/505,269
09/507,811
09/512,529
09/521,525
09/521,288
09/859,826
09/543,194
09/543,192
09/566,890

4A. Patent Application Numbers CONT'D.

09/752,222
09/568,356
09/568,751
09/596,493
09/607,389
09/607,391
09/608,302
09/608,304
09/610,277
09/631,089
09/633,532
09/633,958
09/661,745
09/661,821
09/661,822
09/711,198
09/723,847
09/751,897
09/757,121
09/684,266
09/769,773
09/681,160
09/811,982
09/815,508
09/817,929
09/834,118
09/834,819
09/865,083
09/892,002
09/896,945
09/928,559
09/797,391
60/245,610
09/871,255
60/257,646
60/252,715
60/259,000
60/258,414
60/258,296
06/256,783
60/249,854
60/264,415
60/259,362

4A. Patent Application Numbers CONT'D.

60/280,035
60/280,680
60/283,103
60/285,180
60/289,371
60/300,208
60/300,364
60/301,767
60/302,907
60/315,846
60/323,827
60/309,645
60/312,573
60/325,622
60/325,660
09/743,071
09/869,084
60/308,521
60/273,980

4B. Patent Numbers CONT'D.

5,075,092
4,851,358
4,868,133
5,178,720
5,206,004
5,211,931
5,288,366
5,373,807
5,290,342
5,340,437
5,376,890
5,377,451
5,408,951
5,417,767
5,422,316
5,439,523
5,445,679
5,488,924
5,494,849
5,937,312
5,516,730
5,712,198
5,518,549
5,550,374
5,571,373
5,573,680
5,578,284
5,628,823
5,582,642
5,588,993
5,592,295
5,593,494
5,593,498
5,766,341
5,593,505
5,626,159
5,605,487
5,622,568
5,855,859
5,632,666
5,653,799

4B. Patent Numbers CONT'D.

5,665,159
5,656,078
5,668,045
5,834,812
5,676,751
5,679,055
5,735,258
5,746,834
5,753,567
5,762,491
5,765,890
5,770,522
5,779,791
5,787,595
5,789,309
5,791,493
5,792,273
5,795,381
5,799,728
5,814,148
5,816,274
5,827,113
5,837,662
5,839,460
5,840,120
5,840,202
5,843,234
5,843,322
5,846,318
5,849,076
5,865,670
5,870,881
5,882,402
5,882,989
5,885,344
5,891,250
5,894,711
5,904,768
6,214,109
5,906,533
5,908,504
5,910,295
5,913,975

4B. Patent Numbers CONT'D.

5,919,303
5,919,311
5,922,127
6,053,974
5,935,328
5,942,032
5,948,699
5,964,953
5,968,263
5,974,680
5,975,998
5,976,247
6,180,220
6,006,736
6,006,738
6,015,335
6,019,838
6,026,963
6,030,887
6,039,801
6,039,807
6,057,170
6,063,235
6,074,947
6,086,678
6,089,285
6,093,913
6,100,167
6,112,738
6,114,245
6,120,350
6,129,048
6,135,863
6,168,961
6,171,391
6,177,279
6,164,299
6,179,950
6,183,553
6,187,089
6,189,546
6,191,010
6,197,111

4B. Patent Numbers CONT'D.

6,200,908
6,203,611
6,203,614
6,210,640
6,214,704
6,227,944
6,236,104
6,238,483
6,241,818
6,257,954
6,294,469
6,287,380
6,254,672
5,919,302
6,190,631
6,284,039
6,284,040
6,284,384
6,285,011
6,287,382

RELEASE OF SECURITY INTERESTS

WHEREAS, pursuant to the Patent Security Agreement made as of November 13, 2001 (the "November Patent Security Agreement"), by and among MEMC Electronic Materials, Inc. (the "Borrower") and each of the Borrower's subsidiaries listed on Schedule I to the November Patent Security Agreement (together with the Borrower, the "November Grantors") and Citicorp USA, Inc. ("Citicorp"), as collateral agent for the Secured Parties (as defined therein), the November Grantors granted to Citicorp for the benefit of such Secured Parties a continuing security interest in the Patents (as defined therein); and

WHEREAS, pursuant to the Patent Security Agreement made as of December 20, 2001 (the "December Patent Security Agreement"), by and among the Borrower and each of the Borrower's subsidiaries listed on Schedule I to the December Patent Security Agreement (together with the Borrower, the "December Grantors") and Citicorp, as collateral agent for the Secured Parties (as defined therein), the December Grantors granted to Citicorp for the benefit of such Secured Parties a continuing security interest in the Patents (as defined therein); and

WHEREAS, pursuant to the Patent Security Agreement made as of March 3, 2003 (the "March Patent Security Agreement" and together with the November Patent Security Agreement and December Patent Security Agreement, the "Patent Security Agreements"), by and among the Borrower and each of the Borrower's subsidiaries listed on Schedule I to the March Patent Security Agreement (together with the Borrower, the "March Grantors" and collectively with the November Grantors and December Grantors, the "Grantors") and Citicorp, as collateral agent for the Secured Parties (as defined therein and together with the Secured Parties under the November Patent Security Agreement and December Patent Security Agreement, the "Secured Parties"), the March Grantors granted to Citicorp for the benefit of such Secured Parties a continuing security interest in the Patents (as defined therein); and

WHEREAS, the security offered by the Grantors under the Patent Security Agreements includes each of the patent applications and/or registrations identified on Schedule A attached hereto (the "Released Patent Collateral"); and

WHEREAS, the security interests held by Citicorp in the Released Patent Collateral pursuant to the November Patent Security Agreement were recorded in the United States Patent and Trademark Office on November 21, 2001, at Reel 012273, Frame 0145; and

WHEREAS, the security interests held by Citicorp in the Released Patent Collateral pursuant to the December Patent Security Agreement were recorded in the United States Patent and Trademark Office on December 28, 2001, at Reel 012365, Frame 0345; and

WHEREAS, the security interests held by Citicorp in the Released Patent Collateral pursuant to the March Patent Security Agreement were recorded in the United States Patent and Trademark Office on March 19, 2003, at Reel 013964, Frame 0378; and

WHEREAS, pursuant to paragraph 3 of each of the Patent Security Agreements, Citicorp is authorized to terminate and release the security interests it holds for the benefit of the Secured Parties in the Released Patent Collateral;

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, Citicorp does hereby terminate and release any of its rights, title and security interests in and to the Released Patent Collateral and authorizes the recordation of this Release of

Security Interests in the United States Patent and Trademark Office; and, in accordance with paragraph 3 of each of the Patent Security Agreements, Citicorp agrees to reasonably cooperate with any efforts made by a Grantor to terminate the Patent Security Agreements and/or release any security interests in, to or under the subject collateral thereunder at the sole expense of the Grantors.

IN WITNESS WHEREOF, Citicorp has caused this RELEASE OF SECURITY INTERESTS to be executed and delivered as of the 2nd day of August, 2005.

CITICORP USA, INC.

By: *Suzanne Crymes*
Its: SUZANNE CRYMES
Vice President
Dated: 8/02/05

STATE OF NEW YORK)
) SS.
COUNTY OF NEW YORK)

On this 2nd day of August, 2005, before me, appeared Suzanne Crymes, to me personally known, who being by me duly sworn, did say that she/he is the Vice President of Citicorp USA, Inc., that said instrument was signed on behalf of said corporation by authority of its Board of Directors, and acknowledged said instrument to be the free act and deed of said corporation.

IN WITNESS WHEREOF, I have hereunder set my hand and affixed by notarial seal at my office in New York City, the day and year last above written

Denise Perry
Notary Public in and for
said County and State

My Commission Expires:
DENISE C. PERRY
Notary Public State Of New York
No. 01PE6045304
Qualified in Nassau County
Commission Expires: 07/31/20 06

"Certificate filed New York County"

**Schedule A
PATENTS**

<u>SPLR</u>	<u>PAT. OR</u>	<u>GRANT</u>	<u>EXP.</u>	<u>MEMIC</u>	<u>INVENTOR(S)</u>	<u>TITLE</u>	<u>SPLR</u>	<u>MEMIC (US)</u>
<u>FILE</u>	<u>COUNTRY</u>	<u>*APPLN</u>	<u>DATE</u>	<u>YEAR</u>	<u>FILE #</u>			
1493	USA	4,395,389	07/26/83	2002	95-EM46978	Sch	SPLR	MEMIC (US)
						Chemical Disproportionation Process		
1121	USA	4,450,960	05/29/84	2002	89-4337	Johnson	SPLR	MEMIC (US)
						Package		
						Reactions from Silicon Halide - Hydrogen reaction Gases		
1498	USA	4,332,120	07/30/85	2003	95-EM45155	Smith & Nelson	SPLR	MEMIC (US)
						Silane Purification Process		
1512	USA	4,554,141	11/19/85	2004	95-EM45340	Scull & Laurent	SPLR	MEMIC (US)
						Gas Stream Purification		
1119	USA	4,408,096	08/26/86	2003	89-43417	Hill	SPLR	MEMIC (US)
						Generating		
1118	USA	4,622,082	11/11/86	2004	89-4326	Dyson & Rosal	SPLR	MEMIC (US)
						Conditioned Semiconductor Substrates		
1513	US/CIP	4,632,816	12/20/86	2003	95-EM45284	Melick	SPLR	MEMIC (US)
						Process for Production of Silane		
1117	USA	4,666,532	05/19/87	2004	89-4307	Korb, Reed & Shaw	SPLR	MEMIC (US)
						Densifying Silicon Substrate with Oxygen and Halogen		
1116	USA	4,668,330	03/26/87	2005	89-4348	Golden	SPLR	MEMIC (US)
						Furnace Consumption		

5

1334	USA	5,075,092	12/24/91	2008	95-EM4563A	Brown, Richards & Bossler III	Process for Preparation of Silane	SPLR	MEMC (US)
1065	USA	4,851,358	07/25/89	2008	89-12175-1-1	Haber	Semiconductor Water Fabrication with Improved Control of Internal	SPLR - US	MEMC (US)
1066	USA(DIV)	4,808,133	09/19/89	2008	89-12175-1	Haber	Semiconductor Water Fabrication with Improved Control of Internal Gallering Sites Using RTA	SPLR	MEMC (US)
1072	USA	5,178,720	01/12/93	2011	91-0100	Frederick	Method for Controlling Oxygen Content of Silicon Crystals Using	SPLR	MEMC (US)
1344	USA	5,206,004	04/27/93	2010	95-EM6158A	Park	Silane Compositions and Process	SPLR	MEMC (US)
1345	USA	5,211,931	05/18/93	2012	95-EM6517	Allen & Richards	Removal of Ethylene From Silane Using A Distillation Step After	SPLR	MEMC (US)
1095	USA	5,288,366	02/22/94	2012	91-0950	Holder	Method for Growing Multiple Single Crystals And Apparatus	SPLR	MEMC (US)
1318	USA(DIV)	5,373,807	12/20/94	2012	93-1050	Holder	Method for Growing Multiple Single Crystals and Apparatus For Use Therein	SPLR	MEMC (US)
1347	USA	5,290,342	03/01/94	2011	95-EM6157A	Willeman, Park & Sivily	Silane Compositions and Process	SPLR	MEMC (US)
1313	USA	5,340,437	08/23/94	2013	93-0500	Eck & Vandamme	Process and Apparatus for Etching Semiconductor Wafers	SPLR	MEMC (US)
1301	USA	5,376,880	12/27/94	2013	93-0650	Kewill, Burgdorf,	Capacitive Distance Measuring Apparatus Having Liquid Ground	SPLR	MEMC (US)

Patent No.	Country	Amount	Date	Year	Class	Inventor	Applicant	Agent	IPC Class
1173	USA	5,377,451	01/03/95	2013	92-0600	Leon, Morgan	Water Polishing Apparatus and Method	SPLR	MEMC (US)
1399	USA	5,408,951	04/25/95	2013	94-1050	Tanida	Improved Method for Growing Silicon Crystal	SPLR	MEMC (US)
1312	USA	5,417,767	05/23/95	2013	93-0550	Simon	Water Carrier	SPLR	MEMC (US)
1326	USA	5,422,316	06/06/95	2014	93-0900	Desai, Wranicki & Golland	Semiconductor Water Polisher and Method	SPLR	MEMC (US)
1314	USA	5,439,523	08/08/95	2014	93-0600	Yamaguchi	Device for Suppressing Particle Splash Onto a Semiconductor Wafer	SPLR	MEMC (US)
1246	USA	5,443,679	08/29/95	2012	92-0650	Hansen & Bryan	Plasma Cleaning of Polysilicon for Charging into a Czochralski Crystal Growing Process	SPLR	MEMC (US)
1319	USA	5,488,924	02/06/96	2013	93-0750	Horvath, Jones	Hopper and Method For Use in Charging Semi-Conductor Source	SPLR	MEMC (US)
7606	USA	5,494,849	02/27/96	2015	SSL 94-01	Iyer, Baran,	Single-Batch Slog Process for the Manufacture of Silicon-on-insulator	SPLR	Sibond LLC
7608	US(CIP)	5,537,312	08/10/99	2015	SSI 94-01	Iyer, Baran, Masriani & Craven	Single-Batch Slog Process for the Manufacture of Silicon-on-insulator Substrates	SPLR	Sibond LLC
1363	USA	5,516,730	05/14/96	2014	94-0700	Slive & Pirooz	Pre-Thermal Treatment Cleaning Process	SPLR	MEMC (US)
1652	USA(CONT)	5,712,198	01/27/98	2014	95-2150	Pirooz & Slive	Pre-Heat Treatment Cleaning Process	SPLR	MEMC (US)

1407	USA	5,518,549	05/21/96	2015	94-1450	Hofwig	Suspensor and Bottle Therefor	SPLR	MEMC (US)
1310	USA	5,550,374	08/27/96	2014	94-0150	Holzer & Drescher	Method and Apparatus for Determining Intrinsic Oxygen Content of Relatively Large Diameter Silicon Crystals by Infrared Spectroscopy	SPLR	MEMC (US)
1315	USA	5,571,373	11/05/96	2014	93-0700	Vega, Winkler	Method of Rough Polishing Semiconductor Wafers to Reduce	SPLR	MEMC (US)
1356	USA	5,573,680	11/12/96	2014	94-0900	Shaw & Holzer	Apparatus and Method for Etching a Semiconductor Material Without Altering Flow Pattern Defect Distribution	SPLR	MEMC (US)
1367	USA	5,578,284	11/26/96	2015	94-0800	Chandrasekhar	Process For Eliminating Dislocations In the Neck of A Silicon	SPLR	MEMC (US)
1799	USA(DIV)	5,628,823	02/13/97	2015	96-1150	Chandrasekhar, Kim	A Silicon Single Crystal Having Eliminated Dislocation in its Neck Crystal	SPLR	MEMC (US)
1417	USA	5,582,642	12/10/96	2015	94-1900	Korn, Williams, Schenker & Laidler	Apparatus and Method for Adjusting The Position of A Pull Wire of A Crystal Pulling Machine	SPLR	MEMC (US)
1412	USA	5,588,993	12/31/96	2015	94-1650	Holder	Method for Preparing Molten Silicon Melt from Polycrystalline	SPLR	MEMC (US)
1411	USA	5,592,295	01/07/97	2015	94-1600	Stanton & Krause	Apparatus and Method for Semiconductor Wafer Edge Inspection	SPLR	MEMC (US)
1392	USA	5,593,494	01/14/97	2015	94-1700	Falser	Precision Controlled Precipitation of Oxygen in Silicon	SPLR	MEMC (US)
1462	USA	5,593,498	01/14/97	2015	95-0800	Kimbel, Korn &	Apparatus and Method for Rotating A Crucible of a Crystal	SPLR	MEMC (US)

1871	USA(DIV)	5,766,341	06/16/98	2015	95-0800(DIV)	Kemble, Karb & Hall	Method for Rotating A Crucible of A Crystal Pulling Machine	SPLR	MEMC (US)
1380	USA	5,593,505	01/14/97	2015	94-0900	Ek, Barrman,	Apparatus and Method for Cleaning Semiconductor Wafers	SPLR	MEMC (US)
1826	USA(DIV)	5,626,159	05/06/97	2015	96-1300	Ek, Barrman, Hollander & Chai	Apparatus and Method for Cleaning Semiconductor Wafers	SPLR	MEMC (US)
1331	USA	5,605,487	02/23/97	2014	93-1400	Hilman, Walsh	Semiconductor Wafer Polishing Apparatus and Method	SPLR	MEMC (US)
1317	USA	5,622,588	04/22/97	2014	93-1000	Slive & Pirooz	Cleaning of Metals from Solution	SPLR	MEMC (US)
1874	USA	5,853,859	01/05/99	2014	93-1000(CIP)	Slive & Pirooz	Cleaning Agent	SPLR	MEMC (US)
1366	USA	5,632,666	05/27/97	2014	94-0350	Perrullo & Leonl	Method and Apparatus for Automated Quality Control in	SPLR	MEMC (US)
1444	USA	5,633,799	08/03/97	2015	94-1250	Fuerhoff	System and Method for Controlling Crystal Growth	SPLR	MEMC (US)
1735	USA(DIV)	5,665,159	09/09/97	2015	96-0300	Fuerhoff	System and Method for Controlling Growth of a Silicon Crystal	SPLR	MEMC (US)
1445	USA	5,656,078	08/12/97	2015	94-1300	Fuerhoff	Non-Distorting Video Camera for Use With A System for	SPLR	MEMC (US)
7405	USA	5,668,045	09/16/97	2014		Golland, Caven	Process for Stripping Outer Edge of BESOI Wafers	SPLR	SIBOND LLC
7629	USA(DIV)	5,834,812	11/10/98	2014		Golland, Caven & Barrman	Edge Stripped BESOI Wafer	SPLR	SIBOND LLC

1416	USA	5,676,751	10/14/97	2016	94-1750	Bauman, Kohb & Kim	Rapid Cooling of CZ Silicon Crystal Growth System	SPLR	MEMC (US)
1669	USA	5,679,055	10/21/97	2016	95-1900	Greene, Albrock,	Automated Wafer Lapping System	SPLR	MEMC (US)
1773	US	5,735,258	04/07/98	2016	WFO01823	& Horii		SPLR	MEMC (US)
1667	USA	5,746,834	03/05/98	2016	95-1850	Hanley	Method and Apparatus for Purging Barrel Reactors	SPLR	MEMC (US)
1353	USA	5,753,567	05/19/98	2012	94-0400	Hansen & Bauman	Cleaning of Metallic Contaminants From the Surface of	SPLR	MEMC (US)
1487	USA	5,762,491	06/09/98	2015	95-0750	Williams & Lauer	Solid Material Delivery System for a Furnace	SPLR	MEMC (US)
1765	USA	5,765,890	06/16/98	2016	95-2400	Gayford & Taylor	Device for Transferring a Semiconductor Wafer	SPLR	MEMC (US)
1770	USA	5,770,522	06/23/98	2016	96-0200	Bronson	Polishing Block Heater	SPLR	MEMC (US)
1675	US(CONT)	5,779,791	07/14/98	2016	95-2050		Process for Controlling Thermal History of Clichetalk-Grown Silicon	SPLR	MEMC (US)
1638	USA	5,787,595	08/04/98	2016	95-1050	Desai, Adcock,	Method and Apparatus for Controlling Fineness of Polished	SPLR	MEMC (US)
1877	USA	5,789,309	08/04/98	2016	96-0450	Hellwig	Method and System for Monocrystalline Epitaxial Deposition	SPLR	MEMC (US)
1660	USA	5,791,493	08/11/98	2016	95-1500	Meyer	Poly Silicon Particle Classifying Apparatus	SPLR	MEMC (US)

1932	USA	5,792,273	08/11/98	2017	96-3100	Ries, Helwig & Bossi	Secondary Edge Reflector for Horizontal Reactor	SPLR	MEMC (US)
1436	USA	5,795,381	08/18/98	2016	95-0150	Holder	SIO Probe for Real-Time Monitoring and Control of Oxygen During	SPLR	MEMC (US)
1733	USA	5,799,728	09/01/98	2016	95-1450	Blume	Demulsifier	SPLR	MEMC (US)
1671	USA	5,814,148	09/29/98	2016	95-1950	Kim & Allen	Method for Preparing Molten Silicon Melts from Polycrystalline	SPLR	MEMC (US)
1886	USA	5,816,274	10/06/98	2017	96-1650	Burman & Hollander	Apparatus for Cleaning Semiconductor Wafers	SPLR	MEMC (US)
1774	US	5,827,133	10/27/98	2016	WFO1874	Obama, Iosh	Cutting Machine	SPLR	MEMC (US)
2027	USA	5,837,662	11/17/98	2017	97-1000	Choi, Etk	Post-Lapping Cleaning Process for Silicon Wafers	SPLR	MEMC (US)
1924	USA	5,839,460	11/24/98	2017	96-2250	Choi & Watson	Apparatus for Cleaning Semiconductor Wafers	SPLR	MEMC (US)
1364	USA	5,840,120	11/24/98	2016	94-0750	Kim, Shaw, Chandrasekhar & Scheinker	Apparatus and Method for Controlling Nucleation of Oxygen Precipitates in Silicon Crystals	SPLR	MEMC (US)
1664	USA	5,840,202	11/24/98	2016	95-1750	Wetsh	Apparatus and Method for Shaping Polishing Pads	SPLR	MEMC (US)
1662	USA	5,843,234	12/01/98	2016	95-1650	Finn & Hedwig	Method and Apparatus for Aiming A Barrel Resistor Nozzle	SPLR	MEMC (US)
1911	USA	5,843,322	12/01/98	2016	96-1952	Chandler, Jr.	Process for Etching N, P, N+ and P+ Type Slugs and Wafers	SPLR	MEMC (US)

1771	USA	5,856,318	12/08/98	2016	96-0250	Javid	Method and System for Controlling Growth of a Silicon Crystal	SPLR	MEMC (US)
1764	USA	5,849,076	12/15/98	2016	95-2300	Gayford & Mueller	Cooling System and Method for Epitaxial Barrel Reactor	SPLR	MEMC (US)
2021	USA	5,865,670	02/02/99	2017	97-0350	Frank, Durkin, Bronson & Heim	Water Demurrer Apparatus	SPLR	MEMC (US)
2016	USA	5,870,881	02/16/99	2017	96-2750	Rice, Sudduth Edwards & Roberts	Box Closing Apparatus	SPLR	MEMC (US)
2039	USA	5,882,402	03/16/99	2017	97-1650	Fuerhoff	Method and System for Controlling Growth of a Silicon Crystal	SPLR	MEMC (US)
1334	USA	5,882,989	03/16/99	2017	94-0450	Falser	Process for the Preparation of Silicon Wafers Having a Controlled	SPLR	MEMC (US)
1768	USA	5,883,344	03/23/99	2017	96-0100	Kim & Chandrasekhar	Method and Apparatus for Non-Draft Neck Process for Single Crystal	SPLR	MEMC (US)
2072	USA	5,891,250	04/06/99	2018	97-2150	Louie & Torack	Injector for Reactor	SPLR	MEMC (US)
1999	USA	5,894,711	04/20/99	2017	97-0850	Davidson, Lunday, Hampton, Lent, Anderson & Shive	Box Handling Apparatus and Method	SPLR	MEMC (US)
1434	USA	5,904,768	05/18/99	2016	95-0100	Holder	Process and Apparatus for Controlling the Oxygen Content in	SPLR	MEMC (US)
2396	US(DIV)	6,214,109	04/10/03	2016	95-0100(DIV)		Apparatus for Controlling The Oxygen Content in Silicon Wafers Heavily Doped with Antimony or Arsenic	SPLR	MEMC (US)

2061	USA (CONT)	5,906,533	05/25/99	2016	95-0550 (CONT)	Harris, Hall	Radical Polishing Block Heater	SPLR	MEMC (US)
1490	USA	5,906,504	06/01/99	2015	95-0930	Hanley	Method for Tuning Barrel Reactor Purge System	SPLR	MEMC (US)
1876	USA	5,910,295	06/08/99	2017	96-0390	Deluca	Closed Loop Process for Producing Polycrystalline Silicon and	SPLR	MEMC (US)
2075	USA	5,913,975	06/22/99	2018	97-2800	Holder	Crucible and Method of Preparation Thereof	SPLR	MEMC (US)
2028	USA	5,919,303	07/06/99	2017	97-1050	Holder	Process for Preparing A Silicon Melt From a Polysilicon Charge	SPLR	MEMC (US)
1381	USA	5,919,311	07/06/99	2016	94-0930	Shive & Malik	Control of SiO ₂ Etch Rate Using Dilute Chemical Etchants in the	SPLR	MEMC (US)
2038	USA	5,922,127	07/13/99	2017	97-1200	Lauer & Ferry	Heat Shield For Crystal Puller	SPLR	MEMC (US)
2352	US(DIV)	6,053,974	04/23/00	2017	97-1200 (DIV)	Lauer & Ferry	Heat Shield For Crystal Puller	SPLR	MEMC (US)
1878	USA	5,935,328	08/10/99	2017	96-0600	Cherka, Korb,	Apparatus for Use in Crystal Pulling	SPLR	MEMC (US)
1923	USA	5,942,032	08/24/99	2017	96-2200	Kim, Lauer, Ferry,	Heat Shield Assembly and Method of Growing Vacancy Rich	SPLR	MEMC (US)
7633	USA	5,948,699	09/07/99	2017	99-97-01	Lawrence, Banal	Water Backing Insert for Free Mount Semiconductor Polishing Apparatus and Process	SPLR	Sibond LLC

2019	USA	5,964,953	10/12/99	2018	97-0200	Meitlago	Post-Etching Alkaline Treatment Process	SPLR	MEMC (US)
1920	USA	5,968,263	10/19/99	2018	96-1600	Grover & Kimbel	Open-Loop Method and System for Controlling Growth of	SPLR	MEMC (US)
2359	US(DIV)	69,370,349*		PEND.	96-1600(DIV)		Open Loop Apparatus for Controlling Crystal Growth	SPLR	MEMC (US)
2041	US(DIV)	5,974,680	11/02/99	2016	93-0200	Auderson & Wilson	Apparatus for Use in Cleaning Wafers	SPLR	MEMC (US)
2023	USA	5,975,908	11/02/99	2017	97-0700	Onimed	Wafer Processing Apparatus	SPLR	MEMC (US)
1352	USA	5,976,247	11/02/99	2015	94-0350	Hansen, Shelby,	Surface-Treated Crucibles For Improved Zero Dislocation	SPLR	MEMC (US)
2105	US(CIP)	6,180,220	01/20/01	2017	95-2350(CIP)		Ideal Oxygen Precipitating Silicon Wafers and Oxygen Out-Diffusion-Less Process Therefor	SPLR	MEMC (US)
2008	US(A)(CONT)	09,704,803*		PEND.	95-2352 (cont. of 2105)		Ideal Oxygen Precipitating Epitaxial Silicon Wafers and Oxygen Out-Diffusion-Less Process Therefor	SPLR	MEMC (US)
2082	US	6,006,736	12/28/99	2016					
1885	USA	6,006,738	12/28/99	2017	W72130M004			SPLR	MEMC (US)
1933	USA	6,015,335	01/18/00	2017	97-0100	Roberts	Apparatus for Dressing Abrasive Diamond Saws	SPLR	MEMC (US)
1887	USA	6,019,638	02/01/00	2018	96-1700	Cavalli	Crystal Growing Apparatus with Heat-Coupling Facility	SPLR	MEMC (US)

1650	USA	6,026,963	02/22/00	2016	95-0850	Gray & Cooke	Melture Barrier Bag Having Window	SPLR	MEMC (US)
2407	USA	6,030,867	02/29/00	2017	97-0600	Diesel, Vadnais	Filtration Process for Epitaxial Semiconductor Wafer	SPLR	MEMC (US)
2156	USA	6,030,801	03/21/00	2018	98-0900	Holder & Johnson	Continuous Oxidation Process for Crystal Pulling Apparatus	SPLR	MEMC (US)
2529	EPG	9994481.9*		2019					
2633	US(CONT)	09480481*		PEND.		Holder & Johnson	Continuous Oxidation Process for Crystal Pulling Apparatus	SPLR	MEMC (US)
1931	USA	6,039,807	03/21/00	2018	96-2900	Guarnino, Magon,	Apparatus for Moving Exhaust Tube of Barrel Reactor	SPLR	MEMC (US)
2241	USA	6,057,170	05/02/00	2019	98-3900	Wine	Method and System of Measuring Waivers in Silicon Wafers	SPLR	MEMC (US)
0991	USA	6,063,235	05/16/00	2018	FS-98-002	Taylor	Gas Discharge Apparatus for Water Etching System	SPLR	Phasari LLC
1090	USA	6,074,947	6/13/00	2018	FS-98-001	Munola	Process for Improving Uniform Thickness of Semiconductor Substrates Using Plasma Assisted Chemical Etching	SPLR	Phasari LLC
2154	USA	6,086,678	07/11/00	2019	98-0900	Wilson, Ripz	Pressure Equalization System for Chemical Vapor Deposition	SPLR	MEMC (US)
2069	USA	6,080,285	07/18/00	2018	97-1750	Dastgheib, Esfah,	Method and System for Supplying Semiconductor Source	SPLR	MEMC (US)
2024	USA	6,093,913	07/23/00	2018	97-0800	Schneker & Lauer	Electrical Resistance Heater for Crystal Growing Apparatus	SPLR	MEMC (US)
2171	USA	6,100,167	08/08/00	2017	97-0350	Falster, Lamit,	Process for the Removal of Copper From Polished Boron	SPLR	MEMC (US)

2233	USA	6,112,738	09/08/00	2019	98-3600	Wife, Ragan	Method of Sliding Silicon Wafers for Laser Marking	SPLR	MEMC (US)
2477	US(CONT)	6,114,245	09/05/00	2017	96-2850(CONT)	Vandamme, Xin & Pei	Method of Processing Semiconductor Wafers	SPLR	MEMC (US)
2393	USA	6,120,350	09/19/00	2019	98-5450	Zhou & Davis	Apparatus and Process for Reconditioning Polishing Pads	SPLR	MEMC (US)
2076	USA	6,129,048	10/10/00	2018	97-2990	Sullivan	Improved Susceptor for Barrel Reactor	SPLR	MEMC (US)
2256	USA	6,135,863	10/24/00	2019	98-3990	Zhang, Vogelsong	Method of Conditioning Water Polishing Pads	SPLR	MEMC (US)
1922	USA	6,168,961	01/02/01	2018	96-2050	Vacari	Process for the Preparation of Epitaxial Wafers for Resistivity	SPLR	MEMC (US)
2153	USA	6,171,391	01/09/01	2018	98-0450	Ruehrof, Berman	Method and System for Controlling Growth of a Silicon Crystal	SPLR	MEMC (US)
2077	USA	6,177,279	01/23/01	2018	97-3000	Sun & Adams	Ion Extraction Process and Apparatus for Single-Side Wafers	SPLR	MEMC (US)
2724	US(DIV)	6,184,299	12/26/00	2018	97-3000(DIV)		Ion Extraction Process for Single-Side Wafers		
2233	USA	6,179,930	01/30/01	2019	98-2000	Zhang, Vogelsong	Polishing Pad and Process for Forming Same	SPLR	MEMC (US)
2071	USA	6,183,553	02/06/01	2018	97-1950	Holler, Joslin	Process and Apparatus for Preparation of Silicon Crystals With	SPLR	MEMC (US)
2071.1	US(ACONT)	09/03/03*		PEND.	97-1951		Process and Apparatus for Preparation of Silicon Crystals With Reduced Metal Content	SPLR	MEMC(US)

2152	USA	6,187,089	02/13/01	2019	97-3400	Phillips, Kelcor	Tungsten Doped Crustle and Method for Preparing Same	SPLR	MEMC (US)
2473	USA	6,189,546	02/20/01	2019	99-0450	Zhang, Bruner, Est	Polishing Process for Manufacturing Doped-Stralton-Free Polished	SPLR	MEMC (US)
2407	US FOREIGN	6,191,010	02/20/01	2019	98-3100	Falser	Ideal Oxygen Precipitating Silicon Wafers and Oxygen	SPLR	MEMC (US)
2890	US (CONT)	09/04,000*		PEND.	98-3701		Ideal Oxygen Precipitating Silicon Wafers and Oxygen Out-Diffusion-Less Process Therefor	SPLR	MEMC (US)
2289	USA	6,197,111	03/06/01	2019	98-4600	Ferry & Lehl	Heat Shield Assembly for Crystal Puller	SPLR	MEMC (US)
2074	USA	6,200,908	03/13/01	2019	97-2350	Vandamme, Desai,	Process for Reducing Wariness in Semiconductor Wafers	SPLR	MEMC(US)
2493	USA	6,203,611	03/20/01	2019	99-2450	Kimbel, Wyand, DL	Method of Controlling Growth of a Semiconductor Crystal to	SPLR	MEMC (US)
2384	USA	6,203,614	03/20/01	2019	98-5000	Cierko	Cable Assembly for Crystal Puller	SPLR	MEMC (US)
2000	USA	6,210,640	04/03/01	2018	97-1150	Ruh & Schmidt	Collector for an Automated On-Line Bath Analysis System	SPLR	MEMC (US)
2672	USA(DIV)	09/30,171*		PEND.	97-1151		Process for Collecting and Analyzing the Content of a Liquid in an Automated On-Line Bath Analysis System	SPLR	MEMC(US)
2673	USA(DIV)	09/30,172*		PEND.	97-1152		Process for Collecting and Analyzing the Content of a Liquid in an Automated On-Line Bath Analysis System	SPLR	MEMC(US)

2499	US (FORMAL)	6,214,704	04/10/01	2019	98-1050	Kim	Method of Processing Semiconductor Wafers to Build a Back	SPLR	MEMC (US)
2190	USA	6,237,944	05/08/01	2019	98-1650	Kim, Yeshinara,	Method and Pressure Feeding Machine for Processing A	SPLR	MEMC (US)
2190.1	US (DIV)	09/533,759*		PEND.	98-1650(DIV)		Pressure Feeding Machine for Processing a Semiconductor Wafer	SPLR	MEMC (US)
2312	US FORMAL	6,236,104	5/22/01	2019	98-3050	Falser	Silicon on Insulator Structure From Low Defect Density	SPLR	MEMC (US)
2312.1	US(CONT)	09/737,715*		PEND.	98-3051		Silicon on Insulator Structure From Low Defect Density Single Crystal Silicon	SPLR	MEMC (US)
2387	USA	6,238,483	05/29/01	2019	99-0100	Cherba	Apparatus for Supporting A Semiconductor Layer During Growth	SPLR	MEMC(US)
2385	USA	6,241,818	06/05/01	2019	98-3650	Kimbel & Wyand III	Method and System of Controlling Taper in a Semiconductor	SPLR	MEMC (US)
2318	USA	6,237,954	07/10/01	2020	99-2300	Ng, Walsh, Elk	Apparatus and Process for High Temperature Water Edge Polishing	SPLR	MEMC (US)
1096	USA	6,204,469	09/25/01	2020	PS-88-007	Kulkarni, Deepai	Silicon Wetting Process Flow	SPLR	Pharmashil LLC
1339	USA (CONT)	08/971,233*		PEND.	94-0200	Shive & Pirooz	Cleaning Process for Hydrophobic Silicon Wafers	SPLR	MEMC (US)
1880	USA	08/991,799*		PEND.	96-0950	Davis & Smith	Process for the Control of NO _x Generated by Etching of	SPLR	MEMC (US)
2100	USA	6,287,380	09/11/01	2018	96-0050	Falser & Holzer	Low Defect Density Single Crystal Silicon	SPLR	MEMC (US)
2100.1	US(CONT)	09/833,777*		PEND.	96-0051	Falser & Holzer	Low Defect Density Silicon And a Process for Producing Low Defect		

2101	US(C)IP	6,351,672	07/03/01	2018	96-0030(CIP)	Falser, Holzer,	Density Silicon Wherein V/Ge Is Controlled by Controlling Heat Transfer at the Mol/Solid Interface	SPLR	MEMC (US)
2101.1	US(C)CONT	09/016,015*		PEND.	96-0032		Process for Producing Low Defect Density, Self-Incidental Dominated Silicon		
2614	US(DIV)	09/475,320*		PEND.	96-0030(DIV)		Wherein V/Ge Is Controlled by Controlling Heat Transfer at the Mol/Solid Interface		
							Low Defect Density, Self-Incidental Dominated Silicon		
(2130)									
2130	USA	5,919,302	07/06/99	2017	98-0930	Falser, Holzer,	Low Defect Density, Vacancy Dominated Silicon	SPLR	MEMC (US)
2410	US(C)IP	09/270,366*		PEND.	98-0930(CIP)		Vacancy Dominated, Defect-Free Silicon	SPLR	MEMC (US)
(2131)									
2131	USA	6,190,631	02/20/01	2018	97-2700	Falser, Holzer,	Low Defect Density, Ideal Oxygen Precipitating Silicon	SPLR	MEMC (US)
2889	US(C)CONT	09/703,092*		PEND.	97-2701		Low Defect Density, Ideal Oxygen Precipitating Silicon	SPLR	MEMC (US)
2553	US FORMAL	6,284,039	09/04/01	2019	98-0700	Muller-Seygna, Fei	Epitaxial Silicon Withers Substantially Free of	SPLR	MEMC (US)
2553.1	US(C)CONT	09/074,487		PEND.	98-0701	Muller-Seygna, Fei	Epitaxial Silicon Withers Substantially Free of	SPLR	MEMC (US)
						Holzer, Kohb	Grown-In Defects		
						& Falser			
2191	USA	6,284,040	09/04/01	2019	98-1400	Holder &	Process of Stacking and Melting Polycrystalline Silicon for	SPLR	MEMC (US)

2343	USA	6,284,384	09/04/03	2019	98-3750	Wilson, Ross	An Epitaxial Silicon Wafer With Intrinsic Genuing and a	SPLR	MEMC (US)
2343.1	USA(DIV)	09/09/04*		PEND.	98-3751	Wilson, Ross & Yang	An Epitaxial Silicon Wafer With Intrinsic Genuing and a Method for The Preparation Thereof	SPLR	MEMC (US)
2397	USA	6,285,011	09/04/01	2019	99-0600	Cherko	Electrical Resistance Heater for Crystal Growing Apparatus	SPLR	MEMC (US)
2073	USA	6,287,382	09/11/01	2018	97-3250	Cherko	Element Assembly for Electrical Resistance Heater Used in	SPLR	MEMC (US)
2172	USA	09/082,906*		PEND.	96-2700	Shue & Vinas	Process for the Removal of Copper and Other Metallic Impurities	SPLR	MEMC (US)
2068.1	USA(CONT)	09/667,909*		PEND.	97-3351		Radio Frequency Identification System and Method for Tracking Silicon Wafers	SPLR	MEMC (US)
2291	USA	09/332,743*		PEND.	98-4200	Yang & Weidus	A Method for the Preparation of an Epitaxial Silicon Wafer With	SPLR	MEMC (US)
2466.1	USA(DIV)	09/601,994*		PEND.	97-0451		Electrical Resistance Heater and Method for Crystal Growing Apparatus	SPLR	MEMC (US)
2467	USA	09/344,003*		PEND.	98-2900	Schneider & Lamer	Crystal Puller for Growing Low Defect Density, Self-Interstitial	SPLR	MEMC (US)
2458	USA	09/344,036*		PEND.	98-4900	Fisher & Voronkov	Process for Preparing Defect Free Silicon Crystals Which Allows	SPLR	MEMC (US)

US also claims priority from 21 827 P-98-1850 and 22687P-98-4310)

for Variability in Process Conditions

2458.1	US (CONT)	09/053,232*	PEND.	98-4301	Falser & Voronkov	Process for Preparing Defect Free Silicon Crystals Which Allows for Variability in Process Conditions	SPLR	MEMC (US)
2471	USA	09/344,709*	PEND.	98-4350	Falser	Process for Growth of Defect Free Silicon Crystals of Arbitrarily Large Diameters at Arbitrary Growth Rates Maximum Throughput	SPLR	MEMC (US)
								(2471 claims priority from 21-98-0350, TP-98-4350 and also MEMC 23101P-98-4900)
2232	USA	09/352,980*	PEND.	98-1950	Anderson	Process for Fabricating Semiconductor Wafers With External	SPLR	MEMC (US)
2489	US FORMAL	09/360,850*	PEND.		Falser	Non-Uniform Minority Carrier Lifetime Distributions in High	SPLR	MEMC (US)
2482	US FORMAL	09/372,897*	PEND.	98-4450	Wyand, Euehoff	Apparatus for Accurately Pulling a Crystal and Lifting a Crucible	SPLR	MEMC (US)
2495	US FORMAL	09/379,383*	PEND.	98-3100	Falser	Non-Oxygen Precipitating Coaxial	SPLR	MEMC (US)
2495.1	US (CONT)	09/379,383	PEND.	98-3101	Falser	Non-oxygen Precipitating Coaxial Silicon Wafers	SPLR	MEMC(US)
2500	US FORMAL	09/385,408*	PEND.	98-1500	Falser	Thermally Annealed Wafers Having Improved	SPLR	MEMC (US)
2554	US FORMAL	09/416,098*	PEND.	98-1450	Falser, Binn & Wang	Thermal Annealed, Low Defect Density Single Crystal Silicon	SPLR	MEMC (US)
2482	US FORMAL	09/419,151*	PEND.	98-1350	Holder, Joslin,	Method and System for Measuring Polysulfonic Chuck Size	SPLR	MEMC (US)
2394	USA	09/420,624*	PEND.	98-5900	Schmidt, Seilkep	Apparatus for Cleaning Semiconductor Wafers	SPLR	MEMC (US)

2158	USA	09/438,551*	PEND.	98-1250	Sarfraz & Elk	Etching Solution and Process for Etching Semiconductor Wafers	SPLR	MEMC (US)
2164	USA	09/481,080*	PEND.	99-1350	Vasu, Sarfraz,	Semiconductor Wafer Manufacturing Process	SPLR	MEMC (US)
2691	USA	09/506,105*	PEND.	99-2150	Zhang, Ng & Elk	Semiconductor Wafer Manufacturing Process	SPLR	MEMC (US)
2358	USA	09/495,563*	PEND.	98-5750	Mulil & Voronkov	Method for Controlling Growth of a Silicon Crystal to Minimize	SPLR	MEMC (US)
2632	US FORMAL	09/502,340*	PEND.	99-0900	Furhoff & Kumbel	Method and System for Controlling Diameter of a Silicon Crystal	SPLR	MEMC (US)
2651	USA	09/503,566*	PEND.	00-0050	Holder	Process for Producing a Silicon Mem	SPLR	MEMC (US)
2607	USA	09/505,269*	PEND.	99-3350	Ng, Xia, Elk, Harris,	Process for Reducing Surface Variations for Polished Wafer	SPLR	MEMC (US)
2374	USA	09/507,811*	PEND.	99-1150	Ng & Tashley	Method for Wafer Processing	SPLR	MEMC (US)
1695	USA	09/512,529*	PEND.	PS 98-006	Mitura, Desai, Elk &	A Method of Processing Semiconductor Wafers	SPLR	PharmSII LLC
2689	1st FORMAL	09/521,525*	PEND.	99-0051	Phillips, Kohnen	Doping of Molten Silicon For Use in Crystal Growing Process	SPLR	MEMC (US)
2690	2nd FORMAL	09/521,288*	PEND.	99-0052		Barium Doping of Molten Silicon for Use in Crystal Growing Process		
2690.1	US(DIV)	09/529,826*	PEND.	99-0053		Barium Doping of Molten Silicon for Use in Crystal Growing Process		
2149.1	USA	09/543,194*	PEND.	97-3250	Elk, Stufansen,	Process for Etching a Silicon Wafer	SPLR	MEMC (US)

2187.1	USA	09/543,192*	PEND.	98-1800	Sufamany, Rei, Erik	Method for the Detection of Processing-Induced Defects	SPLR	MEMC (US)
2641	USA	09/566,890*	PEND.	99-3550	Yang, Stanley	Modified Susceptor for Use in Chemical Vapor Deposition Processes	SPLR	MEMC (US)
2643	US (CIP)	09/752,222*	PEND.	99-3850	Ries, Yang & Stanley	An Epitaxial Silicon Water Free From Antidoping and Backside Halo	SPLR	MEMC (US)
2980	USA	09/568,356*	PEND.	99-2200	Chenbo, Brian	Method and Device for Feeding Arsenic Dopant into A Silicon	SPLR	MEMC(US)
2982	USA	09/568,751*	PEND.	99-2400	Banan, Kulkarni	A Multi-Stage Arsenic Doping Process to Achieve Low Resistivity in	SPLR	MEMC (US)
2235.1	FORMAL US	09/596,483*	PEND.	98-2150	Kojima, Isai	Process for Preparing Single Crystal Silicon Having Uniform	SPLR	MEMC (US)
2294	USA	09/607,389*	PEND.	98-4700	Tomek, Rics	A Method and Apparatus for Forming an Epitaxial Silicon Water	SPLR	MEMC(US)
2294.1	USDIV	to be filed		98-4701				
2292	USA	09/607,391*	PEND.	98-4280	Yang	A Method and Apparatus for Forming A Silicon Water with a	SPLR	MEMC (US)
2293	USA	09/608,302*	PEND.	98-4650	Wilson, Rics	Method and Apparatus for Forming a Silicon Water with a Denuded Zone	SPLR	MEMC (US)
2983	USA	09/608,304*	PEND.	99-2250	Williams, Andrus, Kulaga, Harrell	Non-Contaminating Gas-Tight Valve for Semiconductor Applications	SPLR	MEMC (US)
2294.1	FORMAL US	09/610,277*	PEND.	98-3650	Basic & Iltig	Polishing Mixture and Process for Reducing Incorporation of Copper Into	SPLR	MEMC (US)

3322	USA	09/631,489*	PEND.	99-2850	Lu, Frank, Edwards	Method of Polishing a Semiconductor Wafer	SPLR	MEMC (US)
2737	USA	09/633,532*	PEND.	00-2350	Zhang, Eric, Ragon,	Method for Processing a Semiconductor Wafer Using Double-Side Polishing	SPLR	MEMC(US)
2644	USA	09/633,958*	PEND.	99-3650	Zhang, Xin, Bi,	Method and Apparatus for a Wafer Carrier Having an Inert		
2443.1	US (FORMAL)	09/661,745	PEND.	99-1750	McCullum, Alexander,	Process for Suppressing the Nucleation and/or Growth of Interstitial	SPLR	MEMC (US)
2443.3	U.S. FORMAL	09/661,823*	PEND.	99-1650	Mule-Sergio, Libera	Method for Producing Coaxial Silicon Free of Agglomerated	SPLR	MEMC (US)
2442.1	FORMAL US	09/661,822*	PEND.	99-1600	Mule-Sergio & Falser	Process for Detecting Agglomerated Intrinsic Point Defects by	SPLR	MEMC (US)
2704	USA	09/711,108*	PEND.	98-5800	Fuerthert, Boman, Holder	Method and Apparatus for Preparing Molten Silicon Melt From Polycrystalline Silicon Charge	SPLR	MEMC(US)
2642	USA	09/723,847*	PEND.	99-3600	Ruprecht	Defect Classification Using Scattered Light Intensities at Various Angles	SPLR	MEMC(US)
2763	USA	09/751,897*	PEND.	00-0900	Ries	Semiconductor Wafer Holder	SPLR	MEMC(US)
2702	USA	09/757,121*	PEND.	99-3950	Swedaramuthy Banan, Holder & Ferry	Crystal Puller and Method for Growing Single Crystal Semiconductor Material	SPLR	MEMC (US)
2810	USA	09/684,266*	PEND.	00-0100	Ferry, Kimbel,	Heat Shield Assembly for Crystal Pulling Apparatus	SPLR	MEMC(US)
2728	USA	09/769,773*	PEND.	00-0400	Stefanescu, Brangenberg & Duly	Method and Apparatus for Reconditioning a Shipping Container	SPLR	MEMC(US)

2784	USA	09/06/1,160*	PEND.	00-2150	Anderson, Schmidt, Tresler, Buser & Callahan	Method and Apparatus to Place Wafers into and Out of Machine	SPLR	MEMC(US)
2904	USA	09/01/1,982*	PEND.	00-3400	Phillips, Dredell, & McCallum	Crystal Puller and Method for Growing Monocrystalline Silicon Ingots	SPLR	MEMC(US)
2381	USA	09/01/5,508*	PEND.	99-2250	Ferry, Schenker Barna	Heat Shield Assembly for Crystal Puller	SPLR	MEMC(US)
2300	USA	09/01/7,029*	PEND.	99-2600	Shannon	Method for Evaluating A Wafer Cleaning Operation	SPLR	MEMC(US)
2919	USA	09/03/4,118*	PEND.	00-2900	Inamoto, Lark, Schmidt, Spier, Stanton	Method of Calibrating a Semiconductor Wafer Drying Apparatus	SPLR	MEMC(US)
2182	USA	09/03/4,819*	PEND.	00-1750	Blume	System and Method for Reconditioning a Chiller	SPLR	MEMC(US)
2765	USA	09/06/5,083*	PEND.	00-2300	Fai, Yang	A Method for Calibrating Nanotopographic Measuring Equipment	SPLR	MEMC(US)
2803	USA	09/09/2,002*	PEND.	00-3550	Lu, Banna, Tao, Ferry & Chelko	Crystal Puller and Method for Growing Monocrystalline Silicon Ingots	SPLR	MEMC(US)
2892	USA	unknown*	PEND.	01-1000	Alivisatos, Fujii, Vedants	Polishing Apparatus, Polishing Head and Method	SPLR	MEMC(US)

2987	USA	unknown*	PEND.	00-29960	Ng, Jose, Hendrik, Albrecht	Apparatus and Process for Producing Polished Semiconductor Wafers	SPLR	MEMC(US)
2323.1	US: FORMAL	09/096,395*	PEND.	99-1100	Kulkarni, Ekn, Schmidt	Process for Etching a Silicon Wafer	SPLR	MEMC(US)
2788.1	US: FORMAL	09/928,539*	PEND.	98-2350	Zhang, Eric, Xin	Method for Processing a Semiconductor Wafer Using Two-Stage	SPLR	MEMC(US)
2739.1	US FORMAL	09/797,391*	PEND.	00-0700	Keller	Statistical Control Method for Proportions with Small Sample Sizes	SPLR	MEMC(US)
2579	US PROCV (related to 2340)	60/245,610*	11/2001	99-1800	Falser, Vorenkov	Process for Preparing Low Defect Density Silicon Using High Growth Rates	SPLR	MEMC(US)
2379.1	US FORMAL	09/871,253*	PEND.	99-1861				
2808	US PROCV	60/257,646*	12/2001	00-1100	Holder, McGuire, Burger	Process for Monitoring the Gaseous Environment of a Crystal Puller for Semiconductor Growth	SPLR	MEMC(US)
2340	US PROCV (related to 2579)	60/252,715*	11/2001	98-5400	Vorenkov, Falser, Banam	A Method for the Production of Low Defect Density Silicon	SPLR	MEMC(US)
2340.1	US FORMAL	unknown*	PEND.	98-5401				
2440	US PROCV	60/259,000*	12/2001	99-1050	Mahr, Muller-Siegrin Fehl, Banam	Silicon Wafers Substantially Free of Oxidation Induced Sticking Faults	SPLR	MEMC(US)

214	US PROV	60/258,414*	12/2001	00-1050	Ree, Wilson, Staudley Shive, Rossi	Semiconductor Wafer Manufacturing Process	SPLR	MEM(CUS)
2441	US PROV	60/251,296*	12/2001	99-1250	Steinbarthmuthy, Braun, Holder	Apparatus and Process for the Preparation of Low-iron Single Crystal Silicon Substantially Free of Agglomerated Intrinsic Point Defects	SPLR	MEM(CUS)
2462	US PROV	60/256,783*	12/2001	98-6050	Falster	Process for Recleaning Semiconductor Wafers and Reclaimed Wafers	SPLR	MEM(CUS)
2811	US PROV	60/249,844*	11/2001	00-2750	Konami, Wilson	High Throughput Epitaxial Growth by Chemical Vapor Deposition	SPLR	MEM(CUS)
2960	US PROV	60/264,115*	01/2002	01-0150	Xiao, Kimbel Libbert & Braun	Low Defect Density Silicon Substantially Free of Oxidation Induced Stacking Faults	SPLR	MEM(CUS)
2806	US PROV	60/259,363*	01/2002	00-1480	Falster, Vorobkov, Mauri & Benoit	Process for Preparing Single Crystal Silicon Having Improved Gas Oxide Integrity	SPLR	MEM(CUS)
2890	US PROV	60/280,035*	03/2002	00-0450	Veau, Stefanesca, Torack & Wilson	Thermal Annealing Process for Producing Silicon Wafers With Improved Surface Characteristics	SPLR	MEM(CUS)
2321	US PROV	60/280,680*	03/2002	99-2750	Grabbe, Deane	Solution Compositions and Process for Etching Silicon	SPLR	MEM(CUS)
2764	US PROV	60/283,103*	04/2002	00-1650	Brins	Control of Thermal Donor Formation in High Resistivity CZ Silicon	SPLR	MEM(CUS)
2748	US PROV	60/285,180*	04/2002	00-1600	Beghini, Gambino, Ravani, Riet, Sacchini & Staudley	A Method for the Preparation of an Epitaxial Silicon Wafer with Intrinsic Generating	SPLR	MEM(CUS)

1094	US PROV	60/289,371*	05/2002	99-004	Anderson & Haler	Plasma Assisted Chemical Etching Process and Apparatus for Improving Fineness of Semiconductor Wafers	SPLR	Phasmati LLC
2984	US PROV	60/300,208*	06/2002	01-1130	Palser	Process for Producing Silicon on Insulator Structure Having Intrinsic Gauging by Ion Implantation	SPLR	MEMC(US)
2985	US PROV	60/300,364*	06/2002	01-1450	Binus	Silicon on Insulator Structure From High Resistivity CZ Silicon	SPLR	MEMC(US)
2311	US PROV	60/291,767*	07/2002	98-4950	Kimbel, Johnson, Kim, McCallum, Alexander & Huber	Process for Preparing Defect Free Silicon by Controlling the Average Axial Temperature	SPLR	MEMC(US)
2640	US PROV	60/302,907*	07/2002	99-3450	Shive	Process for Making Wafers for Ion Implantation	SPLR	MEMC(US)
2973	US PROV	60/315,846*	08/2002	01-0300	Speedburrmanby & Nishimura	Process for Eliminating Neck Dislocations During Czochralski Crystal Growth	SPLR	MEMC(US)
2972	US PROV	60/313,827*	09/2002	00-3750	Petro, Porfiri, Seale, Yonakov, Coliava	Analytical Method to Measure Nitrogen Concentration in Single Crystal Silicon	SPLR	MEMC(US)
2981	US PROV	60/309,645*	08/2002	99-0350	Phillips, Keiner & Holder	Method of Eliminating Near-Surface Bubbles in Quartz Crucibles	SPLR	MEMC(US)
2804	US PROV	60/312,573*	8/2002	00-1500	Javidi	Controlled Crown Growth Process for Czochralski Single Crystal Silicon	SPLR	MEMC(US)
2970	US PROV	60/325,622*	9/2002	01-0250	Kulkarni, Baman,	Process for Preparing an Arsenic-Doped Silicon Single Crystal Silicon Using a Non-Consumable Dopant Feeder	SPLR	MEMC(US)

2971	US PROV	60/323,640*	9/2002	01-0200	Kojima, Kazuo, & Luers	Process for Preparing an Atomic-Doped Single-Crystal Silicon Using a Composable Doped Feeder	SPLR	MEMC (US)
2979	US NATL.	09/743,071*	PEND.			Process for Mapping Metal Contaminant Concentration on a Silicon Wafer Surface		
2411.2	US NATL.	09/869,084*	PEND.					
2905.2	US PROV	60/308,531*	7/2002	WP3621M051	& Rosen	Method for Producing the Same		
2469.1	US PROV	60/273,980*	3/2002	01-0100 WP356A054	Kojima, Kazuo	A Method for Growing a Single-Crystal Silicon	SPLR	MEMC (US)